

## Plastic Darlington Complementary Silicon Power Transistors

Plastic Darlington complementary silicon power transistors designed for general purpose amplifier and high-speed switching applications.

- High DC Current Gain  
 $h_{FE} = 1400$  (Typ) @  $I_C$   
 $= 2.0$  Adc
- Collector-Emitter Sustaining Voltage — @ 10 mAdc  
 $V_{CEO(sus)} = 45$  Vdc (Min) — BD776  
 $= 60$  Vdc (Min) — BD777, 778  
 $= 80$  Vdc (Min) — BD780
- Reverse Voltage Protection Diode
- Monolithic Construction with Built-in Base-Emitter output Resistor



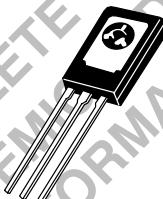
**ON Semiconductor®**

<http://onsemi.com>

**DARLINGTON  
4-AMPERE  
COMPLEMENTARY SILICON  
POWER TRANSISTORS  
45, 60, 80 VOLTS  
15 WATTS**

### MAXIMUM RATINGS

Rating	Symbol	BD776	BD777 BD778	BD780	Unit
Collector-Emitter Voltage	$V_{CEO}$	45	60	80	Vdc
Collector-Base Voltage	$V_{CB}$	45	60	80	Vdc
Emitter-Base Voltage	$V_{EB}$		5.0		Vdc
Collector Current — Continuous Peak	$I_C$		4.0 6.0		Adc
Base Current	$I_B$		100		mAdc
Total Device Dissipation $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$		15 0.12		W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$		−65 to +150		$^\circ\text{C}$



CASE 77-08  
TO-225AA TYPE

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.34	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# BD777

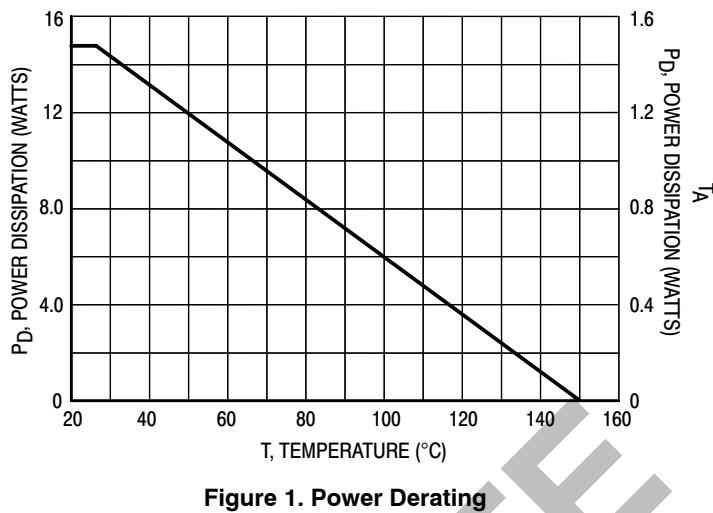


Figure 1. Power Derating

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage (1) ( $I_O = 10 \text{ mA}_\text{dc}$ , $I_B = 0$ )	$V_{CEO(\text{sus})}$	45	—	Vdc
BD776 BD777, BD778 BD780		60	—	
		80	—	
Collector Cutoff Current ( $V_{CE} = 20 \text{ V}_\text{dc}$ , $I_B = 0$ ) ( $V_{CE} = 30 \text{ V}_\text{dc}$ , $I_B = 0$ ) ( $V_{CE} = 40 \text{ V}_\text{dc}$ , $I_B = 0$ )	$I_{CEO}$	—	100	$\mu\text{A}_\text{dc}$
BD776 BD777, BD778 BD780		—	100	
		—	100	
Collector Cutoff Current ( $V_{CB} = \text{Rated}$ , $V_{CEO(\text{sus})}$ , $I_E = 0$ ) ( $V_{CB} = \text{Rated}$ , $V_{CEO(\text{sus})}$ , $I_E = 0$ , $I_C = 100^\circ\text{C}$ )	$I_{CBO}$	—	1.0	$\mu\text{A}_\text{dc}$
		—	100	
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ V}_\text{dc}$ , $I_C = 0$ )	$I_{EBO}$	—	1.0	$\mu\text{A}_\text{dc}$

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 2.0 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ )	$H_{FE}$	750	—	
Collector-Emitter Saturation Voltage ( $I_C = 1.5 \text{ Adc}$ , $I_B = 6 \text{ mA}_\text{dc}$ )	$V_{CE(\text{Sat})}$	—	1.5	Vdc
Base Emitter Saturation Voltage ( $I_C = 1.5 \text{ Adc}$ , $I_B = 6 \text{ mA}_\text{dc}$ )	$V_{BE(\text{Sat})}$	—	2.5	Vdc
Base-Emitter On Voltage ( $I_C = 1.5 \text{ Adc}$ , $V_{CE} = 3 \text{ Vdc}$ )	$V_{BE(\text{On})}$	—	2.3	Vdc
Output Diode Voltage Drop ( $I_{EC} = 2.0 \text{ Adc}$ )	$V_{EC}$	—	2.0	Vdc

## DYNAMIC CHARACTERISTICS

Current Gain Bandwidth Product ( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 2.0 \text{ Vdc}$ )	$f_T$	20	—	MHz
	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Unit</b>
Turn-On Time ( $I_C = 250 \text{ mA}$ , $V_{CE} = 2 \text{ V}$ )	$t_{on}$	—	250	ns
BD775-777 BD776-778-780		—	150	
Turn-Off Time ( $I_C = 250 \text{ mA}$ , $V_{CE} = 2 \text{ V}$ )	$t_{off}$	—	600	ns
BD775-777 BD776-778-780		—	400	

# BD777

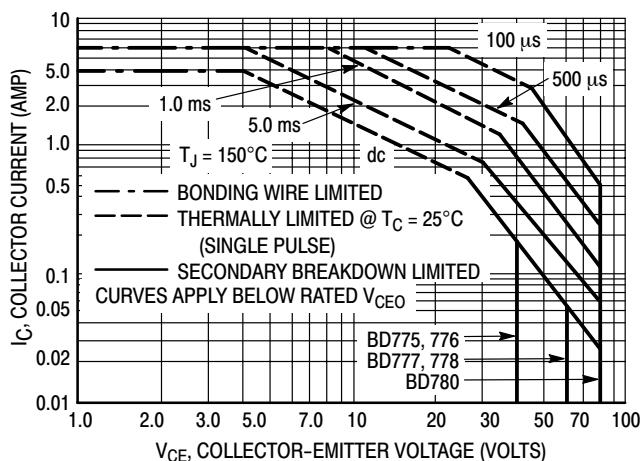


Figure 2. Active Region Safe Operating Area

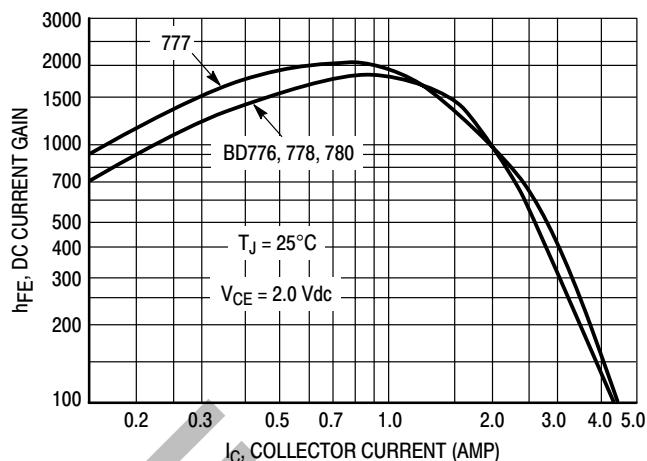


Figure 3. Typical DC Current Gain

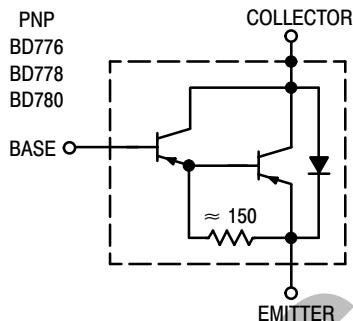
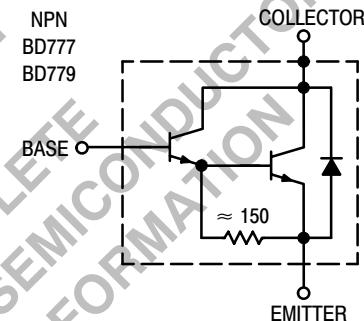
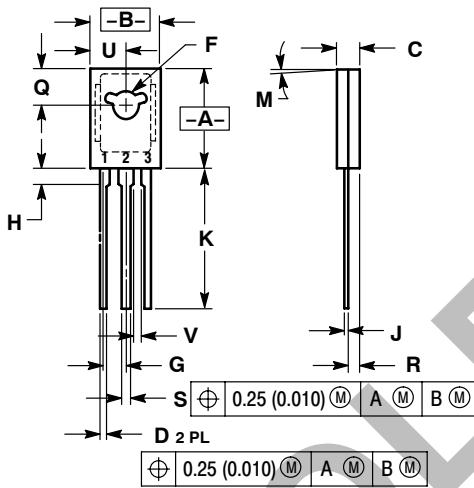


Figure 4. Darlington Circuit Schematic



## PACKAGE DIMENSIONS

CASE 77-08  
TO-225AA TYPE  
ISSUE V

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094	BSC	2.39	BSC
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:  
 1. Emitter  
 2. Collector  
 3. Base

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